ELSEVIER

Journal of Crystal Growth 191 (1998) 911–919

JOURNAL OF CRYSTAL GROWTH

Author index

Abe, K., see Nakanishi, H. 191 (1998) 711
Abramof, E., see Rappl, P.H.O. 191 (1998) 466
Abrutis, A., J.P. Sénateur, F. Weiss, V. Bigelyte, A. Teiserskis, V. Kubilius, V. Galindo and S. Balevicius, High quality $YBa_2Cu_3O_7$ films grown on $LaAlO_3$ by single source pulsed metalorganic chemical vapor deposition 191 (1998) 79
Aiga, M., see Takemi, M. 191 (1998) 18
Alkemper, J., S. Sous, C. Stöcker and L. Ratke, Directional solidification in an aerogel furnace with high resolution optical temperature measurements 191 (1998) 252
An, H.G., see Lee, H. 191 (1998) 59
Angermeier, D., R. Monna, A. Slaoui and J.C. Muller, Analysis of thin film polysilicon on graphite substrates deposited in a thermal CVD system 191 (1998) 386
Anzai, H., S. Maki, S. Takasaki, S. Tanaka, S. Nakatsuji, J.-i. Yamada, K. Nozaki, A. Negishi and M. Harusawa, Effect of electrode-materials for electrocrystallization of organic charge-transfer complex $(TMTSF)_2ClO_4$ 191 (1998) 148
Arkenbout, G.J., see van den Berg, E.P.G. 191 (1998) 169
Asaba, S., see Nakanishi, H. 191 (1998) 711
Asano, T., see Saito, T. 191 (1998) 723

Baars, T., see Höfling, E. 191 (1998) 607
Babu, S.M., see Senguttuvan, N. 191 (1998) 130
Bacchin, G. and T. Nishinaga, Dependence of the degree of selectivity on the Al content during the selective area growth of AlGaAs on GaAs(0 0 1) by PSE/MBE 191 (1998) 599
Baik, H.K., see Choi, D.J. 191 (1998) 718
Balevicius, S., see Abrutis, A. 191 (1998) 79
Bancel, P.A., V.B. Cajipe, F. Rodier and J. Witz, Laser seeding for biomolecular crystallization 191 (1998) 537
Bandeira, I.N., see Rappl, P.H.O. 191 (1998) 466
Barilo, S.N., see Leonyuk, N.I. 191 (1998) 135
Bauhuis, G.J., P.R. Hageman and P.K. Larsen, Heavily doped p-type AlGaInP grown by metalorganic chemical vapor deposition 191 (1998) 313
Bayer, M., see Höfling, E. 191 (1998) 607
Béji, L., see Rebey, A. 191 (1998) 734
Belenko, S.V., see Kurlov, V.N. 191 (1998) 520
Belenko, S.V., see Kurlov, V.N. 191 (1998) 779
Bennema, P., see Bögels, G. 191 (1998) 446
Bennema, P., see Grimbergen, R.F.P. 191 (1998) 846
Bennema, P., see van Hoof, P.J.C.M. 191 (1998) 861
Bennett, B.R., see Twigg, M.E. 191 (1998) 651
Benz, K.W., see Cröll, A. 191 (1998) 365
Bermúdez, V., F. Caccavale, C. Sada, F. Segato and E. Diéguez, Etching effect on periodic domain structures of lithium niobate crystals 191 (1998) 589
Bigelyte, V., see Abrutis, A. 191 (1998) 79
Bischoff, J.L., see Dentel, D. 191 (1998) 697
Boettinger, W.J., see Coriell, S.R. 191 (1998) 573
Bögels, G., see van den Berg, E.P.G. 191 (1998) 169
Bögels, G., H. Meekes, P. Bennema and D. Bollen, The role of {1 0 0} side faces for lateral growth of tabular silver bromide crystals 191 (1998) 446
Bollen, D., see Bögels, G. 191 (1998) 446
Bondarenko, E.A., see Kovalenko, S.I. 191 (1998) 553
Boschetti, C., see Rappl, P.H.O. 191 (1998) 466
Braski, D.N., see Gao, Y. 191 (1998) 439
Bray, K.L., see Koporulina, E.V. 191 (1998) 767
Brecht, E., C. Træholt, R. Schneider and G. Linker, Transmission electron microscopy study of the interface of $Bi_2Sr_2CaCu_2O_{8+\delta}$ thin films on (1 1 0) oriented $SrTiO_3$ substrates 191 (1998) 421
Burger, A., see Chattopadhyay, K. 191 (1998) 377
Buschmann, V., M. Rodewald, H. Fuess, G. Van Tendeloo and C. Schäffer, Hetero-epitaxial growth of $CoSi_2$ thin films on Si(1 0 0): template effects and epitaxial orientations 191 (1998) 430
Bychkov, G.L., see Leonyuk, N.I. 191 (1998) 135

0022-0248/98/$19.00 © 1998 Elsevier Science B.V. All rights reserved.
PII S0022-0248(98)00525-9

Caccavale, F., see Bermúdez, V. 191 (1998) 589
Cajipe, V.B., see Bancel, P.A. 191 (1998) 537
Canselier, J.P., see Lin, C.H. 191 (1998) 791
Canselier, J.P., see Lin, C.H. 191 (1998) 803
Carlsson, N., T. Junno, L. Montelius, M.-E. Pistol, L. Samuelson and W. Seifert, Growth of self-assembled InAs and $InAs_xP_{1-x}$ dots on InP by metalorganic vapour phase epitaxy 191 (1998) 347
Chai, B.H.T., see Morris, R.C. 191 (1998) 108
Champness, C.H., see Shukri, Z.A. 191 (1998) 97
Chattopadhyay, K., S. Feth, H. Chen, A. Burger and C.-H. Su, Characterization of semi-insulating CdTe crystals grown by horizontal seeded physical vapor transport 191 (1998) 377
Chaudhuri, J., see Gao, Y. 191 (1998) 439
Cheema, S.N., see Gao, Y. 191 (1998) 439
Chen, C.-M., L.T. Zhang and W.C. Zhou, Characterization of LaB_6–ZrB_2 eutectic composite grown by the floating zone method 191 (1998) 873
Chen, H., see Chattopadhyay, K. 191 (1998) 377
Chen, N., see Lin, L. 191 (1998) 586
Chen Xingda, see Zhou Guoqing 191 (1998) 517
Cheng, L., Z. Zhang, G. Zhang and Z. Yang, Microstructures of GaN films grown by low pressure metal-organic vapor phase epitaxy on (0 1 $\bar{1}$ 2) sapphire substrates 191 (1998) 641
Cheong, S.-W., see Kloc, Ch. 191 (1998) 294
Choi, D.J., Y.H. Kim, D.W. Han, H.K. Baik and S.I. Kim, Formation of polycrystalline silicon films on glass substrates at low-temperatures by a direct negative Si ion beam deposition system 191 (1998) 718
Choi, D.Y. and S.J. Chung, Annealing behaviors of lattice misfit in YIG and La-doped YIG films grown on GGG substrates by LPE method 191 (1998) 754
Christopher, G.K., A.G. Phipps and R.J. Gray, Temperature-dependent solubility of selected proteins 191 (1998) 820
Chua, S.J., see Li, G. 191 (1998) 357
Chung, S.J., see Choi, D.Y. 191 (1998) 754
Closs, H., see Rappl, P.H.O. 191 (1998) 466
Cook, M.J., see Wankerl, A. 191 (1998) 8
Coriell, S.R., G.B. McFadden, R.F. Sekerka and W.J. Boettinger, Multiple similarity solutions for solidification and melting 191 (1998) 573
Cotta, M.A., see Soares, L.S.M. 191 (1998) 44
Cröll, A., Th. Kaiser, M. Schweizer, A.N. Danilewsky, S. Lauer, A. Tegetmeier and K.W. Benz, Floating-zone and floating-solution-zone growth of GaSb under microgravity 191 (1998) 365
Danilewsky, A.N., see Cröll, A. 191 (1998) 365
Davis, A.M.J., see Hadji, L. 191 (1998) 889
De Carvalho, M.M.G., see Soares, L.S.M. 191 (1998) 44
Deng Peizhen, see Zhou Gueqing 191 (1998) 517
Dennis, M., see Yeckel, A. 191 (1998) 206
Dentel, D., J.L. Bischoff, L. Kubler, J. Werckmann and M. Romeo, Surface smoothing induced by epitaxial Si capping of rough and strained Ge or $Si_{1-x}Ge_x$ morphologies: A RHEED and TEM study 191 (1998) 697
Derby, J.J., see Yeckel, A. 191 (1998) 206
DeSisto, W.J. and B.J. Rappoli, Ultraviolet absorption sensors for precursor delivery rate control for metalorganic chemical vapor deposition of multiple component oxide thin films 191 (1998) 290
Diéguez, E., see Bermúdez, V. 191 (1998) 589
Domagala, J., see Szczerbakow, A. 191 (1998) 673
Domopoulou, A., A. Michaelides, S. Skoulika and D. Kovala-Demertzi, Crystallization of an unstable molecular compound using a tailor-made additive 191 (1998) 166
Dong Jianrong, see Zhou Hongwei 191 (1998) 361
Drevet, B., see Eustathopoulos, N. 191 (1998) 268
Du, J., see Li, Y.X. 191 (1998) 282
Duan, L.H., see Xu, D.P. 191 (1998) 646
Durose, K., see Szczerbakow, A. 191 (1998) 673
Dutta, P.S. and A.G. Ostrogorsky, Nearly diffusion controlled segregation of tellurium in GaSb 191 (1998) 904

Edgar, J.H., see Gao, Y. 191 (1998) 439
El Jani, B., see Rebey, A. 191 (1998) 734
Elliott, R., see Liu, J. 191 (1998) 261
Emerson, D.T., see Wankerl, A. 191 (1998) 8
Eremenko, V.V., see Kovalenko, S.I. 191 (1998) 553
Eustathopoulos, N., B. Drevet and E. Ricci, Temperature coefficient of surface tension for pure liquid metals 191 (1998) 268

Fawell, P.D., see Rossiter, D.S. 191 (1998) 525
Felicelli, S.D., J.C. Heinrich and D.R. Poirier, Three-dimensional simulations of freckles in binary alloys 191 (1998) 879
Ferreira, S.O., see Rappl, P.H.O. 191 (1998) 466
Feth, S., see Chattopadhyay, K. 191 (1998) 377
Forchel, A., see Höfling, E. 191 (1998) 607
Fuess, H., see Buschmann, V. 191 (1998) 430
Fukuda, T., see Kaigawa, K. 191 (1998) 119
Fukuda, T., see Kawaguchi, T. 191 (1998) 125
Fukuda, T., see Sato, J. 191 (1998) 746

Gabas, N., see Lin, C.H. 191 (1998) 791
Gabas, N., see Lin, C.H. 191 (1998) 803
Gajbhiye, N.S., see Panda, R.N. 191 (1998) 92
Galindo, V., see Abrutis, A. 191 (1998) 79
Gallagher, H.G., see Ryu, G. 191 (1998) 492
Gan Fuxi, see Zhou Guoqing 191 (1998) 517
Gao, Y., J.H. Edgar, J. Chaudhuri, S.N. Cheema, M.V. Sidorov and D.N. Braski, Low-temperature chemical-vapor deposition of 3C–SiC films on Si(1 0 0) using SiH_4–C_2H_4–HCl–H_2 191 (1998) 439
Garcia, J.A., A. Remón, V. Muñoz and R. Triboulet, Photoluminescence study of radiative transitions in ZnTe bulk crystals 191 (1998) 685
Gardner, J.S., B.D. Gaulin and D.McK. Paul, Single crystal growth by the floating-zone method of a geometrically frustrated pyrochlore antiferromagnet, $Tb_2Ti_2O_7$ 191 (1998) 740
Gaulin, B.D., see Gardner, J.S. 191 (1998) 740
Gebhardt, W., see Hahn, B. 191 (1998) 65
Gibart, P., see Rebey, A. 191 (1998) 734
Giesen, Ch., see Xu, X.G. 191 (1998) 341
Gower, L.A. and D.A. Tirrell, Calcium carbonate films and helices grown in solutions of poly(aspartate) 191 (1998) 153
Gray, R.J., see Christopher, G.K. 191 (1998) 820
Griebl, E., see Hahn, B. 191 (1998) 65
Grimbergen, R.F.P., see Vogels, L.J.P. 191 (1998) 563
Grimbergen, R.F.P., P.J.C.M. van Hoof, H. Meekes and P. Bennema, Morphology of orthorhombic n-paraffin crystals: the influence of multiple connected nets 191 (1998) 846
Grimbergen, R.F.P., see van Hoof, P.J.C.M. 191 (1998) 861
Gurin, V.S., Nucleation and growth of PbS nanocrystals and simulation of X-ray diffraction patterns 191 (1998) 161

Hadji, L. and A.M.J. Davis, The influence of insoluble spherical particles on the stability of a planar solidifying interface 191 (1998) 889
Hageman, P.R., see Bauhuis, G.J. 191 (1998) 313
Hahn, B., E. Pschorr-Schoberer, E. Griebl, M. Kastner and W. Gebhardt, Metalorganic chemical vapor deposition of ZnSe films on glass and GaAs(1 1 1) substrates 191 (1998) 65
Hahn, S.-H., T. Tsukada, M. Hozawa, S. Maruyama, N. Imaishi and S. Kitagawa, Global analysis of heat transfer in Si CZ furnace with specular and diffuse surfaces 191 (1998) 413
Hamadeh, H., see Taudt, W. 191 (1998) 663
Han, D.W., see Choi, D.J. 191 (1998) 718
Han, T.P.J., see Ryu, G. 191 (1998) 492
Hansen, D., see Koporulina, E.V. 191 (1998) 767
Hardt, A., see Taudt, W. 191 (1998) 663
Harusawa, M., see Anzai, H. 191 (1998) 148
Hayashi, Y., see Saito, T. 191 (1998) 723
Heime, K., see Xu, X.G. 191 (1998) 341
Heinrich, J.C., see Felicelli, S.D. 191 (1998) 879
Heuken, M., see Xu, X.G. 191 (1998) 341
Heuken, M., see Taudt, W. 191 (1998) 663
Hicks, R.F., see Kappers, M.J. 191 (1998) 332
Hiei, F., see Tsukamoto, H. 191 (1998) 679
Hirano, T., see Sato, T.J. 191 (1998) 545
Hirsch, L.S., see Ziemer, K.S. 191 (1998) 594
Höfling, E., J.P. Reithmaier, T. Baars, M. Bayer and A. Forchel, Optical and structural properties of GaInAs/InP single quantum wells grown by solid-source MBE with a GaP decomposition source 191 (1998) 607
Hong, K.J., see Lee, H. 191 (1998) 59
Hong, S.K., B.J. Kim, H.S. Park, Y. Park, S.Y. Yoon and T.I. Kim, Evaluation of nanopipes in MOCVD grown (0 0 0 1)GaN/Al_2O_3 by wet chemical etching 191 (1998) 275
Hoogesteger, F.J., see ten Grotenhuis, E. 191 (1998) 834
Hövel, R., see Xu, X.G. 191 (1998) 341
Hozawa, M., see Hahn, S.-H. 191 (1998) 413
Huang, J.F., see Jin, P. 191 (1998) 285
Huang, J.Y., see Wu, H.Z. 191 (1998) 72
Hunt, J.D., see Maraşli, N. 191 (1998) 558

Ikeda, M., see Tsukamoto, H. 191 (1998) 679
Ilievski, D., see Rossiter, D.S. 191 (1998) 525
Imaeda, M., see Kaigawa, K. 191 (1998) 119
Imaeda, M., see Kawaguchi, T. 191 (1998) 125
Imaishi, N., see Hahn, S.-H. 191 (1998) 413
Ito-Landers, K.M., see Soares, L.S.M. 191 (1998) 44
Ivanov, V.Yu., see Szczerbakow, A. 191 (1998) 673

Jagadish, C., see Li, G. 191 (1998) 357
Jenneskens, L.W., see ten Grotenhuis, E. 191 (1998) 834
Jeong, T.S., see Lee, H. 191 (1998) 59
Jiang, H., see Ning, Y. 191 (1998) 39
Jiang, X.B., see Wu, H.Z. 191 (1998) 72
Jiang Xue-yin, Jin Yang, Zhang Zhi-lin and Xu Shao-hong, Mn-doped nanometer-size ZnS clusters in chitosan film matrix prepared by ion-coordination reaction 191 (1998) 692

Jin, P., M. Tazawa, J.F. Huang and S. Tanemura, Growth of samarium monosulfide thin films by co-sputtering deposition 191 (1998) 285
Jin, W., Z. Pan and Z. Liu, Effect of buoyancy-driven convection upon crystal growth of $KNbO_3$ in the melt 191 (1998) 760
Jin, Y., see Ning, Y. 191 (1998) 39
Jin Yan, see Jiang Xue-yin 191 (1998) 692
Ju, Y.L., see Li, Y.X. 191 (1998) 282
Junno, T., see Carlsson, N. 191 (1998) 347

Kaigawa, K., T. Kawaguchi, M. Imaeda, H. Sakai and T. Fukuda, Crystal structure of LPE-grown $LiNb_{1-x}Ta_xO_3$ epitaxial films 191 (1998) 119
Kaiser, Th., see Cröll, A. 191 (1998) 365
Kameta, M., see Saito, T. 191 (1998) 723
Kamiya, N., see Sugiyama, N. 191 (1998) 84
Kappers, M.J., M.L. Warddrip and R.F. Hicks, Ligand exchange reactions in InGaAs metalorganic vapor-phase epitaxy 191 (1998) 332
Kastner, M., see Hahn, B. 191 (1998) 65
Katoh, Y., see Kubota, E. 191 (1998) 501
Kawaguchi, T., see Kaigawa, K. 191 (1998) 119
Kawaguchi, T., K. Mizuuchi, K. Yamamoto, T. Yoshino, M. Imaeda and T. Fukuda, Fabrication of thin-film waveguide QPM-SHG devices by domain-inverted liquid-phase epitaxy 191 (1998) 125
Kawahara, A., see Saito, T. 191 (1998) 723
Kawasaki, K., see Sawada, T. 191 (1998) 225
Kennedy, R.J., see Stampe, P.A. 191 (1998) 472
Kennedy, R.J., see Stampe, P.A. 191 (1998) 478
Kim, B.J., see Hong, S.K. 191 (1998) 275
Kim, J.Y., see Lee, H. 191 (1998) 59
Kim, K., see Lee, H.J. 191 (1998) 621
Kim, S.I., see Choi, D.J. 191 (1998) 718
Kim, T.I., see Hong, S.K. 191 (1998) 275
Kim, T.S., see Lee, H. 191 (1998) 59
Kim, Y.H., see Choi, D.J. 191 (1998) 718
Kimura, S., see Yoshimura, J. 191 (1998) 483
Kitagawa, S., see Hahn, S.-H. 191 (1998) 413
Kloc, Ch., S.-W. Cheong and P. Matl, Floating-zone crystal growth of perovskite manganites with colossal magnetoresistance 191 (1998) 294
Kokh, A., Crystal growth through forced stirring of melt or solution in Czochralski configuration 191 (1998) 774
Kong, M., see Li, X. 191 (1998) 31
Kong, M., see Li, X. 191 (1998) 34
Kong, M., see Wang, H. 191 (1998) 627
Kong Meiying, see Zhou Hongwei 191 (1998) 361
Koporulina, E.V., see Leonyuk, N.I. 191 (1998) 135
Koporulina, E.V., N.I. Leonyuk, D. Hansen and K.L. Bray, Flux growth and luminescence of Ho : $YAl_3(BO_3)_4$ and $PrAl_3(BO_3)_4$ crystals 191 (1998) 767
Körfer, H., see Taudt, W. 191 (1998) 663
Koutsoukos, P.G., see Spanos, N. 191 (1998) 783
Kovala-Demertzi, D., see Domopoulou, A. 191 (1998) 166
Kovalenko, S.I., D.D. Solnyshkin, E.A. Bondarenko, E.T. Verkhovtseva and V.V. Eremenko, Electron diffraction study on the rise of crystal phase in rare-gas and nitrogen clusters 191 (1998) 553
Kubilius, V., see Abrutis, A. 191 (1998) 79
Kubler, L., see Dentel, D. 191 (1998) 697
Kubota, E., M. Shimokozono and Y. Katoh, LPE growth of yttrium–lutetium, indium–gallium garnet films for optical waveguide formation on a GGG substrate 191 (1998) 501
Kurlov, V.N., S.N. Rossolenko and S.V. Belenko, Growth of sapphire core-doped fibers 191 (1998) 520
Kurlov, V.N. and S.V. Belenko, Growth of sapphire shaped crystals with continuously modulated dopants 191 (1998) 779
Kurnevich, L.A., see Leonyuk, N.I. 191 (1998) 135
Kusakabe, K., see Saito, T. 191 (1998) 723
Kwon, M.S. and J.Y. Lee, Formation of CuPt-type ordered (Cd, Zn)Te at CdTe/ZnTe interface 191 (1998) 51

Lakner, H., see Taudt, W. 191 (1998) 663
LaPierre, R.R., B.J. Robinson and D.A. Thompson, Growth mechanisms of III–V compounds by atomic hydrogen-assisted epitaxy 191 (1998) 319
Larsen, P.K., see Bauhuis, G.J. 191 (1998) 313
Larson Jr., D.J., see Zheng, L.L. 191 (1998) 243
Lauer, S., see Cröll, A. 191 (1998) 365
Laxmanan, V., The limiting behavior of the gradient function for an isolated paraboloid growing in a positive temperature gradient 191 (1998) 298
Lee, C.-R., see Lee, H.J. 191 (1998) 621
Lee, H., T.S. Kim, T.S. Jeong, H.G. An, J.Y. Kim, C.J. Youn, P.Y. Yu, K.J. Hong, H.J. Lee and Y.J. Shin, Growth of zinc selenide single crystal by the modified Piper and Polich sublimation method 191 (1998) 59
Lee, H.J., see Lee, H. 191 (1998) 59
Lee, H.J., H. Ryu, C.-R. Lee and K. Kim, Polytypes in GaN films grown by metalorganic chemical vapor deposition on (0 0 0 1) sapphire substrate 191 (1998) 621
Lee, J.Y., see Kwon, M.S. 191 (1998) 51
Lee, R.T., see Liu, Z. 191 (1998) 1

Leonyuk, N.I., E.V. Koporulina, S.N. Barilo, L.A. Kurnevich and G.L. Bychkov, Crystal growth of solid solutions based on the $YAl_3(BO_3)_4$, $NdAl_3(BO_3)_4$ and $GdAl_3(BO_3)_4$ borates 191 (1998) 135
Leonyuk, N.I., see Koporulina, E.V. 191 (1998) 767
Li, G., K.E. Prince, M. Petravic, S.J. Chua and C. Jagadish, Substrate orientation effect on Zn δ-doping in GaAs grown by metal organic vapour-phase epitaxy 191 (1998) 357
Li, S., see Ning, Y. 191 (1998) 39
Li, X., D. Sun, J. Zhang and M. Kong, GaN epilayers grown at high growth rate using gas source molecular beam epitaxy method 191 (1998) 31
Li, X., D. Sun, J. Zhang, S. Zhu and M. Kong, Properties of GaN epilayers with various growth conditions grown by gas source molecular beam epitaxy 191 (1998) 34
Li, Y.X., Y.L. Ju, H.M. Wang, P.J. Niu, C.C. Tang, J. Du, and G.H. Wu The effect of orientation deviation on pattern distortion in epitaxial buried layer on p-type ⟨1 0 0⟩ silicon substrate 191 (1998) 282
Lin, C.H., N. Gabas, J.P. Canselier and G. Pèpe, Prediction of the growth morphology of aminoacid crystals in solution I. α-Glycine 191 (1998) 791
Lin, C.H., N. Gabas and J.P. Canselier, Prediction of the growth morphology of aminoacid crystals in solutionII. γ-Aminobutyric acid 191 (1998) 803
Lin, L., X. Zhong and N. Chen, Improvement of stoichiometry in semi-insulating gallium arsenide grown under microgravity 191 (1998) 586
Linker, G., see Brecht, E. 191 (1998) 421
Liu, J. and R. Elliott, Numerical modelling of the solidification of ductile iron 191 (1998) 261
Liu, Q., see Taudt, W. 191 (1998) 663
Liu, Z., R.T. Lee and G.B. Stringfellow, Pyrolysis of tertiarybutylamine alone and with trimethylgallium for GaN growth 191 (1998) 1
Liu, Z., see Jin, W. 191 (1998) 760
Lu, C.J., H.M. Shen and Y.N. Wang, The growth and phase transitions of epitaxial $Pb(Zr_{0.95}Ti_{0.05})O_3$ thin films prepared by sputter deposition combined with post-annealing on $SrTiO_3$(1 0 0) 191 (1998) 113

Maeda, H., see Saito, T. 191 (1998) 723
Maeda, S., see Nakanishi, H. 191 (1998) 711
Magno, R., see Twigg, M.E. 191 (1998) 651
Mah, K.W., see Yoon, S.F. 191 (1998) 613
Maki, S., see Anzai, H. 191 (1998) 148
Maraşli, N. and J.D. Hunt, The use of measured values of surface energies to test heterogeneous nucleation theory 191 (1998) 558
Marone, P.A., P. Thiyagarajan, A.M. Wagner and D.M. Tiede, The association state of a detergent-solubilized membrane protein measured during crystal nucleation and growth by small-angle neutron scattering 191 (1998) 811
Marsman, A.W., see ten Grotenhuis, E. 191 (1998) 834
Maruyama, S., see Hahn, S.-H. 191 (1998) 413
Matl, P., see Kloc, Ch. 191 (1998) 294
Matsushita, H. and T. Takizawa, Se vapor pressure dependence of the phase diagram of the $CuGa_{1-x}In_xSe_2$ system 191 (1998) 455
McFadden, G.B., see Coriell, S.R. 191 (1998) 573
Meekes, H., see Bögels, G. 191 (1998) 446
Meekes, H., see Grimbergen, R.F.P. 191 (1998) 846
Meekes, H., see van Hoof, P.J.C.M. 191 (1998) 861
Mendonça, C.A.C., see Soares, L.S.M. 191 (1998) 44
Michaelides, A., see Domopoulou, A. 191 (1998) 166
Mihashi, Y., see Takemi, M. 191 (1998) 18
Miyazawa, S. and T. Tabata, Bi_2O_3–TiO_2 binary phase diagram study for TSSG pulling of $Bi_{12}TiO_{20}$ single crystals 191 (1998) 512
Mizuuchi, K., see Kawaguchi, T. 191 (1998) 125
Mo. Y., Y. Xia and W. Wu, A nucleation mechanism for diamond film deposited on alumina substrates by microwave plasma CVD 191 (1998) 459
Mohan, P., see Senguttuvan, N. 191 (1998) 130
Monna, R., see Angermeier, D. 191 (1998) 386
Montelius, L., see Carlsson, N. 191 (1998) 347
Morikoshi, H., see Sato, J. 191 (1998) 746
Morooka, S., see Saito, T. 191 (1998) 723
Morris, R.C. and B.H.T. Chai, Imperfect low-angle boundaries and fracture in hydrothermally grown berlinite crystals 191 (1998) 108
Motisuke, P., see Rappl, P.H.O. 191 (1998) 466
Muller, J.C., see Angermeier, D. 191 (1998) 386
Muñoz, V., see Garcia, J.A. 191 (1998) 685
Murakami, Y., see Yonenaga, I. 191 (1998) 399
Myers, T.H., see Ziemer, K.S. 191 (1998) 594

Nagai, M., see Tsukamoto, H. 191 (1998) 679
Nakanishi, H., K. Nakazato, S. Asaba, K. Abe, S. Maeda and K. Terashima, Temperature dependence of density of molten germanium measured by a newly developed Archimedian technique 191 (1998) 711
Nakatsuji, S., see Anzai, H. 191 (1998) 148
Nakazato, K., see Nakanishi, H. 191 (1998) 711
Negishi, A., see Anzai, H. 191 (1998) 148

Ning, Y., T. Zhou, B. Zhang, H. Jiang, S. Li, G. Yuan, Y. Tian and Y. Jin, Growth and characterization of InAs-rich GaInAsSb alloys on GaSb substrates by MOCVD 191 (1998) 39
Nishinaga, T., see Bacchin, G. 191 (1998) 599
Nishiyama, Y., see Yokoyama, C. 191 (1998) 827
Niu, P.J., see Li, Y.X. 191 (1998) 282
Nomura, T., see Shimizu, K. 191 (1998) 178
Nomura, T., see Shimizu, K. 191 (1998) 185
Nonaka, M., see Yonenaga, I. 191 (1998) 393
Nozaki, K., see Anzai, H. 191 (1998) 148

Oates, W.A. and H. Wenzl, Foreign atom thermodynamics in liquid gallium arsenide 191 (1998) 303
Okamoto, A., see Sugiyama, N. 191 (1998) 84
Okamoto, Y., Theoretical study on the precursors of group-III nitrides 191 (1998) 405
Okumura, K., see Sugiyama, N. 191 (1998) 84
Omeltchouk, A.R., see Szczerbakow, A. 191 (1998) 673
Ostrogorsky, A.G., see Dutta, P.S. 191 (1998) 904

Palosz, W., Diffusive gas losses from silica glass ampoules at elevated temperatures 191 (1998) 897
Pan Liang, see Zhou Hongwei 191 (1998) 361
Pan, Z., see Jin, W. 191 (1998) 760
Panda, R.N. and N.S. Gajbhiye, Chemical synthesis and magnetic properties of nanocrystalline $FeMoN_2$ 191 (1998) 92
Park, H.S., see Hong, S.K. 191 (1998) 275
Park, Y., see Hong, S.K. 191 (1998) 275
Parkinson, G.M., see Rossiter, D.S. 191 (1998) 525
Paul, D.McK., see Gardner, J.S. 191 (1998) 740
Pèpe, G., see Lin, C.H. 191 (1998) 791
Petravic, M., see Li, G. 191 (1998) 357
Phipps, A.G., see Christopher, G.K. 191 (1998) 820
Pistol, M.-E., see Carlsson, N. 191 (1998) 347
Poirier, D.R., see Felicelli, S.D. 191 (1998) 879
Prince, K.E., see Li, G. 191 (1998) 357
Pschorr-Schoberer, E., see Hahn, B. 191 (1998) 65

Que, D.L., see Wu, H.Z. 191 (1998) 72

Radhakrishnan, K., see Yoon, S.F. 191 (1998) 24
Rai, R.N., see Rai, U.S. 191 (1998) 234
Rai, U.S. and R.N. Rai, Physical chemistry of the organic analog of metal–metal eutectic and monotectic alloys 191 (1998) 234
Ramasamy, P., see Senguttuvan, N. 191 (1998) 130
Rappl, P.H.O., H. Closs, S.O. Ferreira, E. Abramof, C. Boschetti, P. Motisuke, A.Y. Ueta and I.N. Bandeira, Molecular beam epitaxial growth of high quality $Pb_{1-x}Sn_xTe$ layers with $0 \leqslant x \leqslant 1$ 191 (1998) 466
Rappoli, B.J., see DeSisto, W.J. 191 (1998) 290
Ratke, L., see Alkemper, J. 191 (1998) 252
Rebey, A., L. Béji, B. El Jani and P. Gibart, Optical monitoring of the growth rate reduction by CCl_4 during metalorganic vapour-phase epitaxy deposition of carbon doped GaAs 191 (1998) 734
Reithmaier, J.P., see Höfling, E. 191 (1998) 607
Remón, A., see Garcia, J.A. 191 (1998) 685
Ricci, E., see Eustathopoulos, N. 191 (1998) 268
Robinson, B.J., see LaPierre, R.R. 191 (1998) 319
Rodewald, M., see Buschmann, V. 191 (1998) 430
Rodier, F., see Bancel, P.A. 191 (1998) 537
Romeo, M., see Dentel, D. 191 (1998) 697
Rose, D., see Szczerbakow, A. 191 (1998) 673
Rossiter, D.S., P.D. Fawell, D. Ilievski and G.M. Parkinson, Investigation of the unseeded nucleation of Gibbsite, $Al(OH)_3$, from synthetic bayer liquors 191 (1998) 525
Rossolenko, S.N., see Kurlov, V.N. 191 (1998) 520
Rudolph, P., see Sato, J. 191 (1998) 746
Ryu, G. and C.S. Yoon, Seeded supercooled melt growth and polar morphology of organic nonlinear optical crystal, meta-nitroaniline (mNA) 191 (1998) 190
Ryu, G., C.S. Yoon, T.P.J. Han and H.G. Gallagher, Growth and characterisation of $CsLiB_6O_{10}$ (CLBO) crystals 191 (1998) 492
Ryu, H., see Lee, H.J. 191 (1998) 621

Sada, C., see Bermúdez, V. 191 (1998) 589
Saito, T., M. Kameta, K. Kusakabe, S. Morooka, H. Maeda, Y. Hayashi, T. Asano and A. Kawahara, Morphology and semiconducting properties of homoepitaxially grown phosphorus-doped (1 0 0) and (1 1 1) diamond films by microwave plasma-assisted chemical vapor deposition using triethylphosphine as a dopant source 191 (1998) 723
Sakai, H., see Kaigawa, K. 191 (1998) 119
Sakamoto, T., see Yoshimura, J. 191 (1998) 483
Samuelson, L., see Carlsson, N. 191 (1998) 347
Sato, J., H. Takeda, H. Morikoshi, K. Shimamura, P. Rudolph and T. Fukuda, Czochralski growth of $RE_3Ga_5SiO_{14}$ (RE = La, Pr, Nd) single crystals for the analysis of the influence of rare earth substitution on piezoelectricity 191 (1998) 746
Sato, T.J., T. Hirano and A.P. Tsai, Single-crystal growth of the decagonal Al–Ni–Co quasicrystal 191 (1998) 545

Sawada, T., K. Takemura, K. Shigematsu, S. Yoda and K. Kawasaki, Effects of gravity on a free dendrite of NH_4Cl grown by dynamic pressure control 191 (1998) 225
Schäffer, C., see Buschmann, V. 191 (1998) 430
Schneider, R., see Brecht, E. 191 (1998) 421
Schweizer, M., see Cröll, A. 191 (1998) 365
Segato, F., see Bermúdez, V. 191 (1998) 589
Seifert, W., see Carlsson, N. 191 (1998) 347
Sekerka, R.F., see Coriell, S.R. 191 (1998) 573
Sénateur, J.P., see Abrutis, A. 191 (1998) 79
Senguttuvan, N., P. Mohan, S.M. Babu and P. Ramasamy, A study of the optical and mechanical properties of $PbWO_4$ single crystals 191 (1998) 130
Shealy, J.R., see Wankerl, A. 191 (1998) 8
Shen, H.M., see Lu, C.J. 191 (1998) 113
Shiba, T., see Takemi, M. 191 (1998) 18
Shigematsu, K., see Sawada, T. 191 (1998) 225
Shimamura, K., see Sato, J. 191 (1998) 746
Shimizu, K., T. Nomura and K. Takahashi, Crystal size distribution of aluminum potassium sulfate in a batch crystallizer equipped with different types of impeller 191 (1998) 178
Shimizu, K., T. Nomura and K. Takahashi, Crystal size distribution of aluminum potassium sulfate in a profiled, a dished, or a flat bottom crystallizer equipped with a pitched paddle 191 (1998) 185
Shimokozono, M., see Kubota, E. 191 (1998) 501
Shin, Y.J., see Lee, H. 191 (1998) 59
Shou, X., see Wu, H.Z. 191 (1998) 72
Shukri, Z.A. and C.H. Champness, Effect of nonstoichiometry on conductivity type in Bridgman-grown $CuInSe_2$ 191 (1998) 97
Sidorov, M.V., see Gao, Y. 191 (1998) 439
Skoulika, S., see Domopoulou, A. 191 (1998) 166
Slaoui, A., see Angermeier, D. 191 (1998) 386
Smeets, W.J.J., see ten Grotenhuis, E. 191 (1998) 834
Soares, L.S.M., M.A. Cotta, C.A.C. Mendonça, K.M. Ito-Landers and M.M.G. de Carvalho, Equilibrium shape and nucleation on InP(0 0 1) surfaces: effect of surface steps 191 (1998) 44
Sohn, S.H., Interface Madelung constants for isoelectronic impurities: generalized Madelung constants 191 (1998) 143
Solnyshkin, D.D., see Kovalenko, S.I. 191 (1998) 553
Sous, S., see Alkemper, J. 191 (1998) 252
Spanos, N. and P.G. Koutsoukos, The transformation of vaterite to calcite: effect of the conditions of the solutions in contact with the mineral phase 191 (1998) 783
Spek, A.L., see ten Grotenhuis, E. 191 (1998) 834
Stampe, P.A. and R.J. Kennedy, X-ray characterization of MgO thin films grown by laser ablation on yttria-stabilized zirconia 191 (1998) 472
Stampe, P.A. and R.J. Kennedy, X-ray characterization of MgO thin films grown by laser ablation on $SrTiO_3$ and $LaAlO_3$ 191 (1998) 478
Stinespring, C.D., see Ziemer, K.S. 191 (1998) 594
Stöcker, C., see Alkemper, J. 191 (1998) 252
Stringfellow, G.B., see Liu, Z. 191 (1998) 1
Su, C.-H., see Chattopadhyay, K. 191 (1998) 377
Sugiyama, N., A. Okamoto, K. Okumura, T. Tani and N. Kamiya, Step structures and dislocations of SiC single crystals grown by modified Lely method 191 (1998) 84
Sun, D., see Li, X. 191 (1998) 31
Sun, D., see Li, X. 191 (1998) 34
Suzuki, J., see Yoshida, S. 191 (1998) 279
Szczerbakow, A., J. Domagala, D. Rose, K. Durose, V.Yu. Ivanov and A.R. Omeltchouk, Structural defects and compositional uniformity in CdTe and $Cd_{1-x}Zn_xTe$ crystals grown by a vapour transport technique 191 (1998) 673

Tabata, T., see Miyazawa, S. 191 (1998) 512
Takahashi, K., see Shimizu, K. 191 (1998) 178
Takahashi, K., see Shimizu, K. 191 (1998) 185
Takasaki, S., see Anzai, H. 191 (1998) 148
Takeda, H., see Sato, J. 191 (1998) 746
Takemi, M., Y. Mihashi, T. Shiba and M. Aiga, High-resolution X-ray diffraction studies on growth interrupted heterointerfaces grown by metalorganic vapor-phase epitaxy 191 (1998) 18
Takemura, K., see Sawada, T. 191 (1998) 225
Takizawa, T., see Matsushita, H. 191 (1998) 455
Tamamura, K., see Tsukamoto, H. 191 (1998) 679
Tamura, Y., see Yokoyama, C. 191 (1998) 827
Tanaka, S., see Anzai, H. 191 (1998) 148
Tanemura, S., see Jin, P. 191 (1998) 285
Tang, C.C., see Li, Y.X. 191 (1998) 282
Tani, T., see Sugiyama, N. 191 (1998) 84
Taudt, W., J. Xu, A. Hardt, H. Körfer, Q. Liu, H. Hamadeh, H. Lakner, J. Woitok and M. Heuken, Optimization of pre-epitaxial processes to obtain high-quality ZnSe/GaAs heterointerfaces grown in a low-pressure metalorganic vapour-phase epitaxy system 191 (1998) 663
Tazawa, M., see Jin, P. 191 (1998) 285
Tegetmeier, A., see Cröll, A. 191 (1998) 365
Teiserskis, A., see Abrutis, A. 191 (1998) 79

Ten Grotenhuis, E., A.W. Marsman, F.J. Hoogesteger, J.C. van Miltenburg, J.P. van der Eerden, L.W. Jenneskens, W.J. Smeets and A.L. Spek, Solid state structures in spin-coated assemblies of oligo(cyclohexylidene) oxime derivatives and (partly) saturated analogues: an atomic force microscopy study 191 (1998) 834
Terashima, K., see Nakanishi, H. 191 (1998) 711
Thiyagarajan, P., see Marone, P.A. 191 (1998) 811
Thompson, D.A., see LaPierre, R.R. 191 (1998) 319
Tian, Y., see Ning, Y. 191 (1998) 39
Tiede, D.M., see Marone, P.A. 191 (1998) 811
Tirrell, D.A., see Gower, L.A. 191 (1998) 153
Træholt, C., see Brecht, E. 191 (1998) 421
Triboulet, R., see Garcia, J.A. 191 (1998) 685
Tsai, A.P., see Sato, T.J. 191 (1998) 545
Tsukada, T., see Hahn, S.-H. 191 (1998) 413
Tsukamoto, H., K. Tamamura, M. Nagai, Futoshi Hiei and M. Ikeda, Optical characteristics of ZnCdSe/ZnSSe single quantum wells 191 (1998) 679
Twigg, M.E., B.R. Bennett and R. Magno, Morphological instability in InAs/GaSb heterostructures 191 (1998) 651

Ueta, A.Y., see Rappl, P.H.O. 191 (1998) 466
Usui, S., see Yoshimura, J. 191 (1998) 483

Van den Berg, E.P.G., G. Bögels and G.J. Arkenbout, Growth of ε-caprolactam crystals from the melt: The influence of cyclohexanone on the $\{1\,1\,\bar{1}\}$ and $\{1\,1\,0\}$ forms 191 (1998) 169
Van der Eerden, J.P., see ten Grotenhuis, E. 191 (1998) 834
Van Enckevort, W.J.P., see van Hoof, P.J.C.M. 191 (1998) 861
Van Hoof, P.J.C.M., see Vogels, L.J.P. 191 (1998) 563
Van Hoof, P.J.C.M., see Grimbergen, R.F.P. 191 (1998) 846
Van Hoof, P.J.C.M., R.F.P. Grimbergen, H. Meekes, W.J.P. van Enckevort and P. Bennema, Morphology of orthorhombic n-paraffin crystals: a comparison between theory and experiments 191 (1998) 861
Van Miltenburg, J.C., see ten Grotenhuis, E. 191 (1998) 834
Van Tendeloo, G., see Buschmann, V. 191 (1998) 430
Verkhovtseva, E.T., see Kovalenko, S.I. 191 (1998) 553
Vogels, L.J.P., P.J.C.M. van Hoof and R.F.P. Grimbergen, On the roughening transition of anisotropic and (pseudo) hexagonal lattices 191 (1998) 563

Wagner, A.M., see Marone, P.A. 191 (1998) 811
Wakayama, N.I., Quantitative study of crystallization kinetics of hen egg-white lysozyme using magnetic orientation 191 (1998) 199
Wang, C.A., OMVPE growth of GaInAsSb in the 2–2.4 μm range 191 (1998) 631
Wang, H., Y. Zeng, H. Zhou and M. Kong, Triclinic deformation and anisotropic strain relaxation of an InAs film on a GaAs(0 0 1) substrate measured by a series of symmetric double crystal X-ray diffraction 191 (1998) 627
Wang, H.M., see Li, Y.X. 191 (1998) 282
Wang Hongmei, see Zhou Hongwei 191 (1998) 361
Wang Siting, see Zhou Guoqing 191 (1998) 517
Wang, X.J., see Xu, D.P. 191 (1998) 646
Wang, Y.N., see Lu, C.J. 191 (1998) 113
Wankerl, A., D.T. Emerson, M.J. Cook and J.R. Shealy, Wavelength dependence of UV laser selective $Al_xGa_{1-x}As$ growth via adlayer stimulation in OMVPE 191 (1998) 8
Warddrip, M.L., see Kappers, M.J. 191 (1998) 332
Weiss, F., see Abrutis, A. 191 (1998) 79
Wenzl, H., see Oates, W.A. 191 (1998) 303
Werckmann, J., see Dentel, D. 191 (1998) 697
Witz, J., see Bancel, P.A. 191 (1998) 537
Woitok, J., see Taudt, W. 191 (1998) 663
Wu, G.H., see Li, Y.X. 191 (1998) 282
Wu, H.Z., J.Y. Huang, Z.Z. Ye, X.B. Jiang, X. Shou and D.L. Que, Strain relaxation in graded SiGe grown by ultrahigh vacuum chemical vapor deposition (UHVCVD) 191 (1998) 72
Wu, R.H., see Xu, D.P. 191 (1998) 646
Wu. W., see Mo, Y. 191 (1998) 459

Xia. Y., see Mo, Y. 191 (1998) 459
Xu, D.P., H. Yang, L.X. Zheng, X.J. Wang, L.H. Duan and R.H. Wu, Gallium diffusion through cubic GaN films grown on GaAs(1 0 0) at high-temperature using low-pressure MOVPE 191 (1998) 646
Xu, J., see Taudt, W. 191 (1998) 663
Xu Jun, see Zhou Guoqing 191 (1998) 517
Xu Ke, see Zhou Guoqing 191 (1998) 517
Xu Shao-hong, see Jiang Xue-yin 191 (1998) 692
Xu, X.G., Ch. Giesen, R. Hövel, M. Heuken and K. Heime, Surface morphology and growth rate variation of InP on patterned substrates using tertiarybutylphosphine 191 (1998) 341

Yamada, J.-i., see Anzai, H. 191 (1998) 148
Yamamoto, K., see Kawaguchi, T. 191 (1998) 125
Yang, H., see Xu, D.P. 191 (1998) 646
Yang, Z., see Cheng, L. 191 (1998) 641

Ye, Z.Z., see Wu, H.Z. 191 (1998) 72
Yeckel, A., Y. Zhou, M. Dennis and J.J. Derby, Three-dimensional computations of solution hydrodynamics during the growth of potassium dihydrogen phosphate II. Spin down 191 (1998) 206
Yoda, S., see Sawada, T. 191 (1998) 225
Yokoyama, C., Y. Tamura and Y. Nishiyama, Crystal growth rates of tricaprin and trilaurin under high pressures 191 (1998) 827
Yonenaga, I. and M. Nonaka, Czochralski growth of bulk crystals of $Ge_{1-x}Si_x$ alloys II. Si-rich alloys 191 (1998) 393
Yonenaga, I. and Y. Murakami, Segregation during the seeding process in the Czochralski growth of GeSi alloys 191 (1998) 399
Yoon, C.S., see Ryu, G. 191 (1998) 190
Yoon, C.S., see Ryu, G. 191 (1998) 492
Yoon, S.F., P.H. Zhang, H.Q. Zheng and K. Radhakrishnan, The effects of arsenic pressure on the properties of $In_{1-x-y}Ga_xAl_yAs$ layers grown by molecular beam epitaxy 191 (1998) 24
Yoon, S.F., K.W. Mah, H.Q. Zheng and P.H. Zhang, Effects of substrate temperature on the properties of $In_{0.48}Ga_{0.52}P$ grown by molecular-beam epitaxy using a valved phosphorus cracker cell 191 (1998) 613
Yoon, S.Y., see Hong, S.K. 191 (1998) 275
Yoshida, S. and J. Suzuki, High quality GaN grown by a gas-source molecular-beam epitaxy and its electrical property 191 (1998) 279
Yoshimura, J., T. Sakamoto, S. Usui and S. Kimura, X-ray perfection study of Verneuil-grown $SrTiO_3$ crystals 191 (1998) 483
Yoshino, T., see Kawaguchi, T. 191 (1998) 125
Youn, C.J., see Lee, H. 191 (1998) 59
Yu, P.Y., see Lee, H. 191 (1998) 59
Yuan, G., see Ning, Y. 191 (1998) 39
Zeng, Y., see Wang, H. 191 (1998) 627
Zeng Yiping, see Zhou Hongwei 191 (1998) 361
Zhang, B., see Ning, Y. 191 (1998) 39
Zhang, G., see Cheng, L. 191 (1998) 641
Zhang, H., see Zheng, L.L. 191 (1998) 243
Zhang, J., see Li, X. 191 (1998) 31
Zhang, J., see Li, X. 191 (1998) 34
Zhang, L.T., see Chen, C.-M. 191 (1998) 873
Zhang, P.H., see Yoon, S.F. 191 (1998) 24
Zhang, P.H., see Yoon, S.F. 191 (1998) 613
Zhang, Z., see Cheng, L. 191 (1998) 641
Zhang Zhi-lin, see Jiang Xue-yin 191 (1998) 692
Zheng, H.Q., see Yoon, S.F. 191 (1998) 24
Zheng, H.Q., see Yoon, S.F. 191 (1998) 613
Zheng, L.L., D.J. Larson Jr. and H. Zhang, Role of thermotransport (Soret effect) in macrosegregation during eutectic/off-eutectic directional solidification 191 (1998) 243
Zheng, L.X., see Xu, D.P. 191 (1998) 646
Zhong Heyu, see Zhou Guoqing 191 (1998) 517
Zhong, X., see Lin, L. 191 (1998) 586
Zhou Guoqing, Xu Jun, Chen Xingda, Zhong Heyu, Wang Siting, Xu Ke, Deng Peizhen and Gan Fuxi, Growth and spectrum of a novel birefringent α-BaB_2O_4 crystal 191 (1998) 517
Zhou, H., see Wang, H. 191 (1998) 627
Zhou Hongwei, Zeng Yiping, Wang Hongmei, Dong Jianrong, Zhu Zhanping, Pan Liang and Kong Meiying, Growth and transport properties of InAs thin films on GaAs 191 (1998) 361
Zhou, T., see Ning, Y. 191 (1998) 39
Zhou, W.C., see Chen, C.-M. 191 (1998) 873
Zhou, Y., see Yeckel, A. 191 (1998) 206
Zhu, S., see Li, X. 191 (1998) 34
Zhu Zhanping, see Zhou Hongwei 191 (1998) 361
Ziemer, K.S., C.D. Stinespring, L.S. Hirsch and T.H. Myers, Characterization of atomic hydrogen-etched HgCdTe surfaces 191 (1998) 594

ELSEVIER

Journal of Crystal Growth 191 (1998) 920–922

JOURNAL OF CRYSTAL GROWTH

Subject index

Apparatus
- for directional solidification of aluminum–silicon 252
- for forced stirring Czochralski of melt growth 774
- for high pressure optical vessel 827
- for multi-zone Mellen furnace 904
- for protein crystal growth 537
- for pyrochlore anti-ferromagnet growth $Tb_2Ti_2O_7$ 740
- for vertical Bridgman with submerged heater 904

Computer simulation
- of alpha-glycine 791
- of convection 206
- of ductile solidification 261
- of gamma-aminobutyric acid 803
- of heat transfer 413
- of molecular orbitals in gas phase 405
- of thermotransport 243
- of X-ray diffraction 161

Constitutional supercooling
- of a planar solidifying interface 889

Convection 206, 225, 760, 774, 879

Device characterisation
- electronic materials 97, 746
- ferroelectric materials 113
- heterostructures 466
- lasers 275
- quantum dots and wires 347
- quantum wells 679

Diffusional control
- of gallium nitride 646
- of tellurium in gallium antimonide 904

Doping
- of zinc in gallium arsenide 357

Electronic materials, see Device characterization

Epitaxy, see Thin film growth

Etching
- chemical 153, 275, 589, 594
- of low-angle boundaries 108

Eutectic growth
- of aluminum–silicon 252
- of Al–$CuAl_2$ 558
- of LaB_6–ZnB_2 873
- of succinonitrile–carbontetrabromide system 234

Heat flow control, of
- Czochralski growth of silicon 413

Heterostructures, see Device materials

Hydrodynamics, see Convection

Kinetics
- of dendritic growth 298
- of growth 24, 34, 44, 166, 169, 178, 185, 199, 553, 651, 697, 760, 811, 827, 834, 861
- of growth element shaped method 779
- of interface control 18, 143, 166, 178, 282, 347
- of nucleation 178, 185, 421, 525, 811
- of precursor analysis 1
- of sedimentation 199
- of transformation 783

Lasers, see Device characterization

Lasers, crystals for
- alumina 520
- holmium : yttrium aluminum borate 767
- nonlinear optical crystals 135
- sapphire 779

Lysozyme 199

Melt growth technique
- by Bridgman–Stockbarger method
  - of copper zinc diselenide 97
  - of epsilon-caprolactam 169
  - of manganese bismuth 243
- by cold traveling heater mother
  - of zinc telluride 685
- by Czochralski method
  - of alpha-barium borate 517
  - of gallium arsenide 303
  - of lead tungstate 130
  - of lithium niobate 589
  - of rare earth gallium silicon dioxide 746
  - of silicon 413
  - of silicon germanium 393, 399
- by edge-defined film-fed growth
  - of alumina 520
- by floating zone method
  - of decagonal aluminum–nickel–cobalt 545

0022-0248/98/$19.00 © 1998 Elsevier Science B.V. All rights reserved.
PII S0022-0248(98)00526-0

– – of gallium antimonide 365
– – of perovskite manganites 294
– by submerged heater method
– – of gallium antimonide 904
– by super cooled solution
– – of cesium lithium hexaborate 492
– – of meta-nitroaniline 190
– by uniaxial solidification
– – of aluminum–silicon 252
– – of lead–tin 879
– by Verneuil method
– – of strontium titanate 483
– general properties
– – density dependence on temperature 711
– technical methods
– – of gas losses through silica glass 897
Microgravity, growth under
– of ammonium chloride 225
– of gallium antimonide 365
– of gallium arsenide 586
– of manganese bismuth 243
Morphological stability
– of crystal faces 563
– of indium arsenide/gallium antimonide 651

Nucleation
– of aluminum–copper chloride 558
– of detergent solutions 811
– of diamond 459
– of fractures 108
– of gibbsite 525
– of indium phosphide 44
– of n-paraffin 861
– of nanocrystals 161
– of silicon 459
Numbers
– Marangoni 365
– Nusselt 298
– Reynolds 206

Phase diagram, of
– bismuth oxide–titanium oxide 512
– copper gallium diselenide–copper indium diselenide 455
– gallium arsenide 303
– LaB_6–ZnO_2 873
– phase transitions 113
– succinonitrile–carbontetrabromide system 234
– tricaprin 827
– trilaurin 827
Precursor, for
– calcite 153
– gallium nitride growth 1
– nanocrystalline ferrous molybdenum nitride 92
– III-nitrides 405
– YBCO 290
Purification, of
– epsilon-caprolactam 169

Quantum dots and wires, see Device characterization
Quantum wells, see Device characterization

Solid growth technique
– by recapitalisation
– – of iron molybdenum nitride 92
Solution growth technique
– by electrocrystallization
– – of organic superconductor $(TMTSF)_2ClO_4$ 148
– by flux method
– – of beta-barium borate 774
– – of rare earth aluminum borate 135
– by high temperature method
– – of holmium : yttrium aluminum borate 767
– by hydrothermal method
– – of aluminum phosphate 108
– by low temperature method
– – of calcite 783
– – of gibbsite 525
– – of lead sulphide 161
– – of manganese-doped zinc sulphide 692
– – of potassium niobate 760
– – of proteins 820
– – of unstable molecular compounds 166
– by precipitation
– – of silver bromide 446
– by sedimentation
– – of hen-egg white lysozyme 199
– by top seeded solution growth
– – of bismuth titanium oxides 512
Statistical mechanics, molecular theory
– of metals 268
Stefan problem or moving boundary problem
– of indium phosphide 341
– of poly-silicon 386
Superconductivity materials, high T_c
– film
– – of BSCCO 421
– – of YBCO 79, 290
Surface structure
– of α-glycine 791
– of epsilon-caprolactam 169
– of gamma-aminobutyric acid 803

Thin film growth
– by atomic hydrogen assisted epitaxy 319
– by atomic layer epitaxy
– – theory of electrostatic potentials 143
– by chemical beam epitaxy
– – of indium phosphide 44
– by directional ion beam deposition
– – of poly-silicon 718
– by gas source molecular beam epitaxy
– – of gallium nitride 31, 34, 279
– by liquid phase epitaxy
– – of lithium niobium tantalate 119, 125
– – of oligo(cyclohexylidene) oximes 834

– – of yttrium iron garnet 754
– – of yttrium lutetium indium gallium garnet 501
– by molecular beam epitaxy
– – of cobalt disilicide 430
– – of gallium antimonide 651
– – of indium arsenide 361, 627, 651
– – of indium gallium aluminum arsenide 24
– – of indium gallium phosphide 613
– – of lead tin telluride 466
– – of silicon germanium 697
– – of zinc cadmium selenide/zinc sulphur selenide 679
– by pulsed laser deposition
– – of magnesium oxide 472, 478
– by rapid thermal chemical vapor deposition
– – of poly-silicon 386
– by sputtering
– – of BSCCO 421
– – of lead zirconium titanate 113
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of diamond 459, 723
– – – of gallium nitride 641
– – – of silicon carbide 439
– – – of silicon germanium 72
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 8, 599
– – – of cadmium zinc telluride 51
– – – of gallium aluminum indium phosphide 313
– – – of gallium arsenide 357, 734
– – – of gallium indium arsenide antimonide 39. 631
– – – of gallium nitride 1, 275, 621, 646
– – – of indium arsenide phosphide 347
– – – of indium gallium arsenide 332, 607
– – – of indium phosphide 18, 341
– – – of mercury cadmium telluride 594
– – – of YBCO 79, 290
– – – of zinc selenide 65, 663

Vapor growth technique
– by chemical transport
– – of cadmium telluride 377
– by evaporation and condensation
– – of cadmium telluride 673
– – of cadmium zinc telluride 673
– – of paraffin crystals 563
– – of samarium monosulphide 285
– – of silicon carbide 84
– by sublimation
– – of zinc selenide 59
Vapor–liquid solid growth
– of n-paraffin 861